



SamHop Microelectronics Corp.

**STU/D339S**

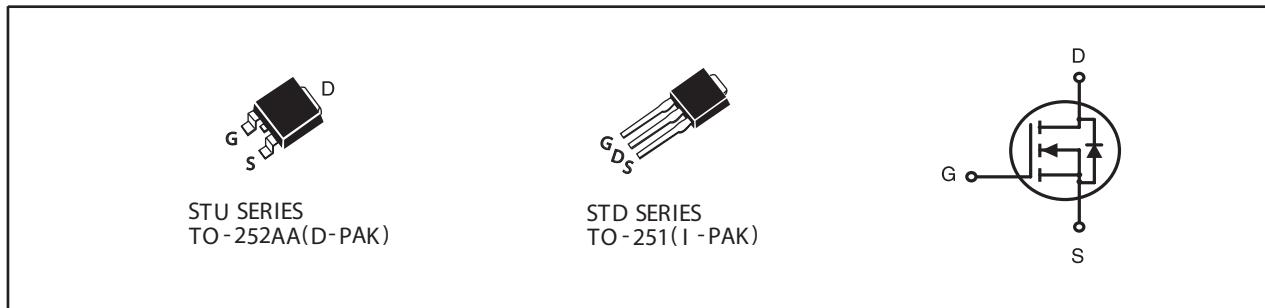
Ver 1.0

## N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
VDSS	ID	RDS(ON) (mΩ) Max
30V	40A	9.6 @ VGS=10V
		15 @ VGS=4.5V

### FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- TO-252 and TO-251 Package.



### ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	$T_C=25^\circ\text{C}$	A
		$T_C=70^\circ\text{C}$	A
$I_{DM}$	-Pulsed <sup>a</sup>	117	A
$E_{AS}$	Single Pulse Avalanche Energy <sup>c</sup>	56	mJ
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	W
		$T_C=70^\circ\text{C}$	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	$^\circ\text{C/W}$

Details are subject to change without notice.

Aug,17,2012

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## ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
I <sub>DS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V			1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0	1.7	3	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =20A		8.2	9.6	m ohm
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =16A		11.5	15	m ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =20A		55		S
<b>DYNAMIC CHARACTERISTICS <sup>b</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V f=1.0MHz		900		pF
C <sub>oss</sub>	Output Capacitance			161		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			124		pF
<b>SWITCHING CHARACTERISTICS <sup>b</sup></b>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V I <sub>D</sub> =1A V <sub>GS</sub> =10V R <sub>GEN</sub> = 6 ohm		17		ns
t <sub>r</sub>	Rise Time			18		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			18		ns
t <sub>f</sub>	Fall Time			46		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V,I <sub>D</sub> =20A,V <sub>GS</sub> =10V		14		nC
		V <sub>DS</sub> =15V,I <sub>D</sub> =20A,V <sub>GS</sub> =4.5V		6.5		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V,I <sub>D</sub> =20A, V <sub>GS</sub> =10V		1.8		nC
Q <sub>gd</sub>	Gate-Drain Charge			4.1		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V,I <sub>s</sub> =2A		0.77	1.3	V
<b>Notes</b>						
a.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
b.Guaranteed by design, not subject to production testing.						
c.Starting T <sub>J</sub> =25°C,L=0.5mH,V <sub>DD</sub> = 20V.(See Figure13)						

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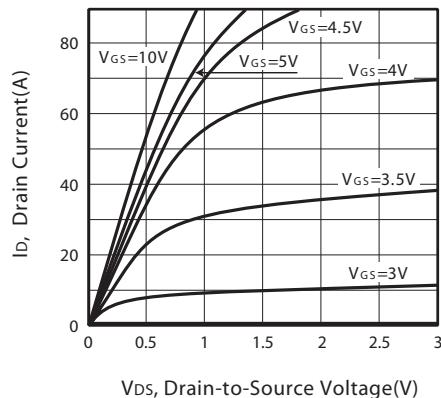


Figure 1. Output Characteristics

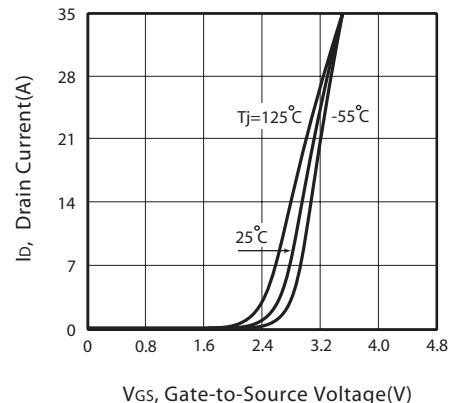


Figure 2. Transfer Characteristics

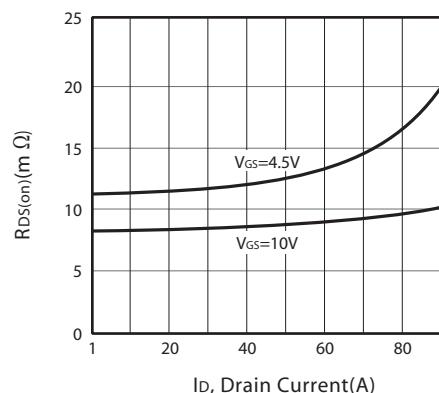


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

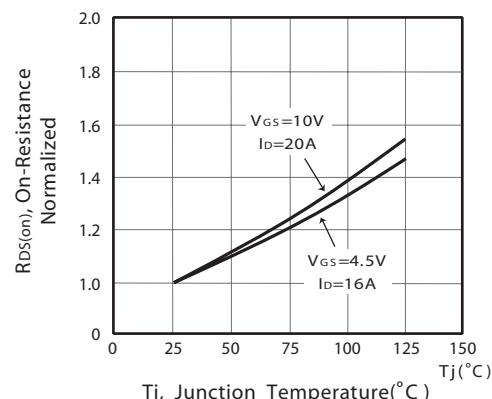


Figure 4. On-Resistance Variation with Drain Current and Temperature

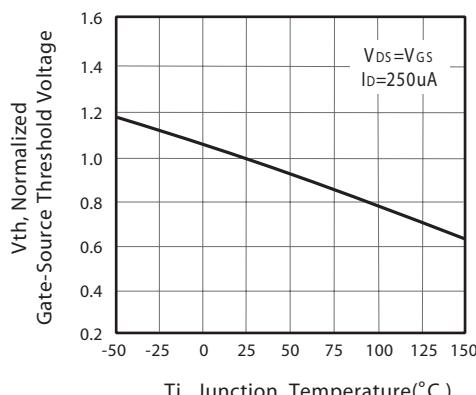


Figure 5. Gate Threshold Variation with Temperature

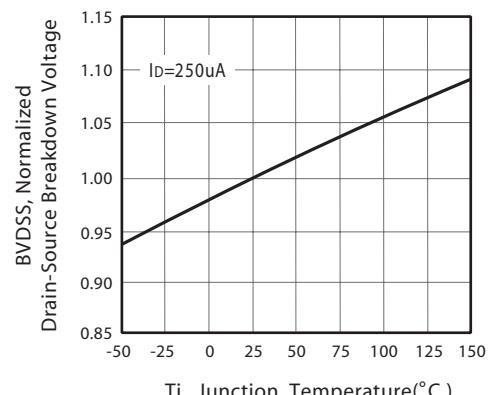
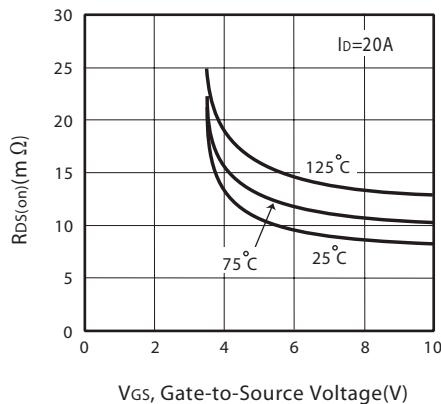
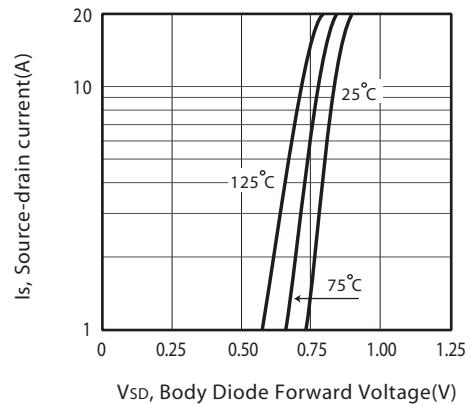


Figure 6. Breakdown Voltage Variation with Temperature



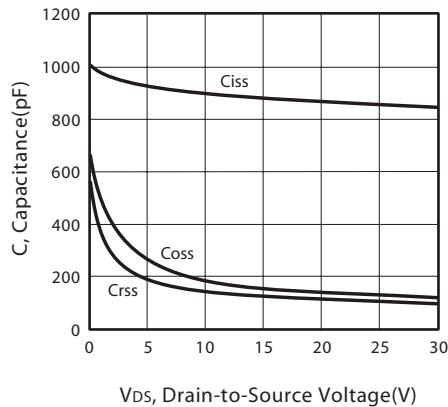
V<sub>GS</sub>, Gate-to-Source Voltage(V)

Figure 7. On-Resistance vs. Gate-Source Voltage



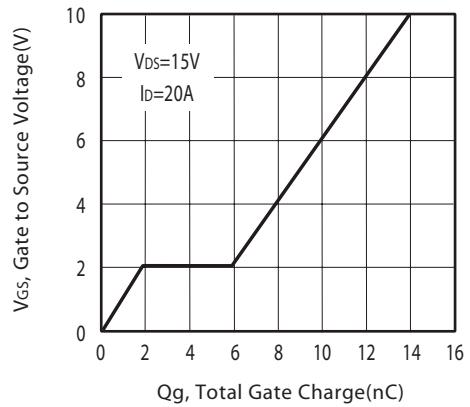
V<sub>SD</sub>, Body Diode Forward Voltage(V)

Figure 8. Body Diode Forward Voltage Variation with Source Current



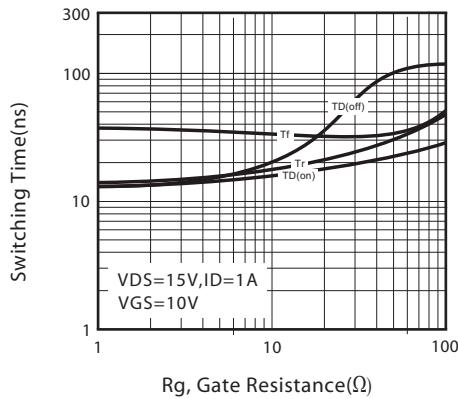
V<sub>DS</sub>, Drain-to-Source Voltage(V)

Figure 9. Capacitance



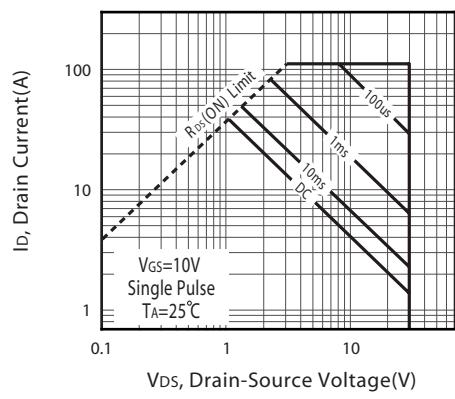
Q<sub>g</sub>, Total Gate Charge(nC)

Figure 10. Gate Charge



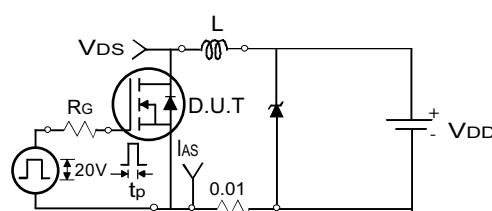
R<sub>g</sub>, Gate Resistance(Ω)

Figure 11. switching characteristics



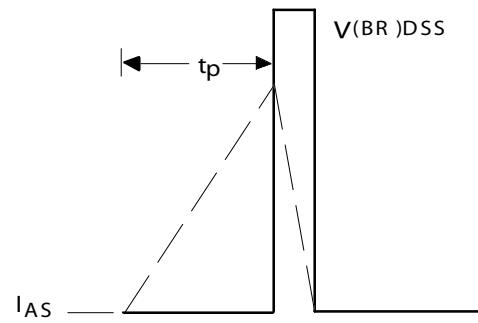
V<sub>DS</sub>, Drain-Source Voltage(V)

Figure 12. Maximum Safe Operating Area



Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

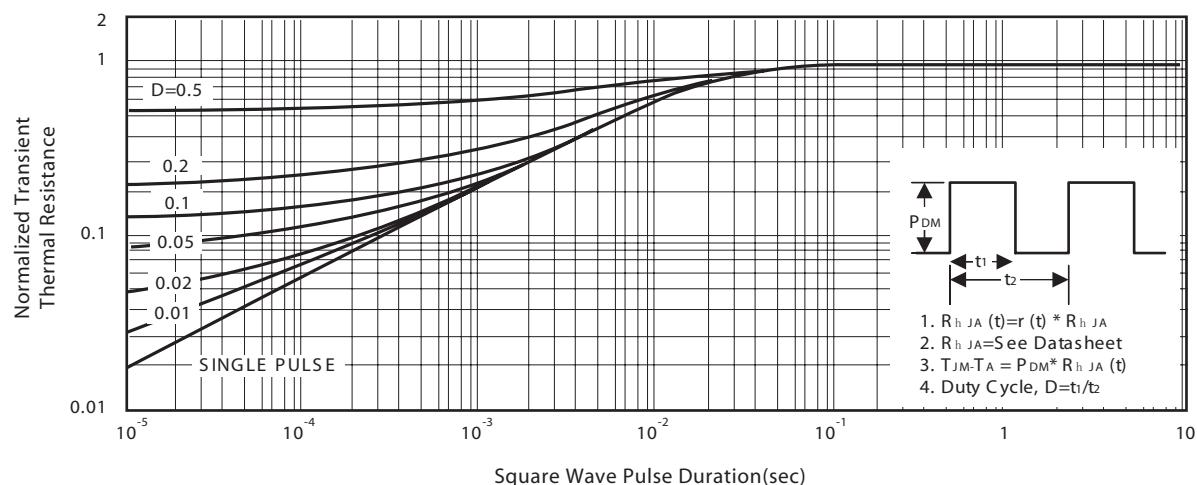
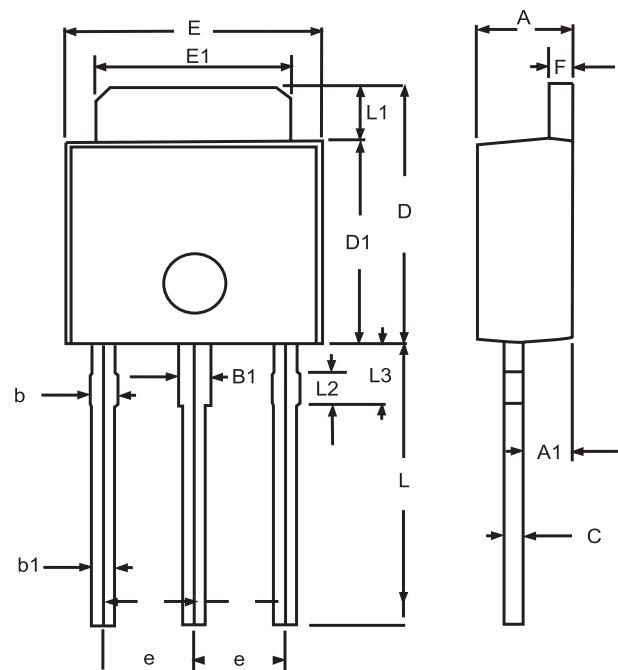


Figure 14. Normalized Thermal Transient Impedance Curve

## PACKAGE OUTLINE DIMENSIONS

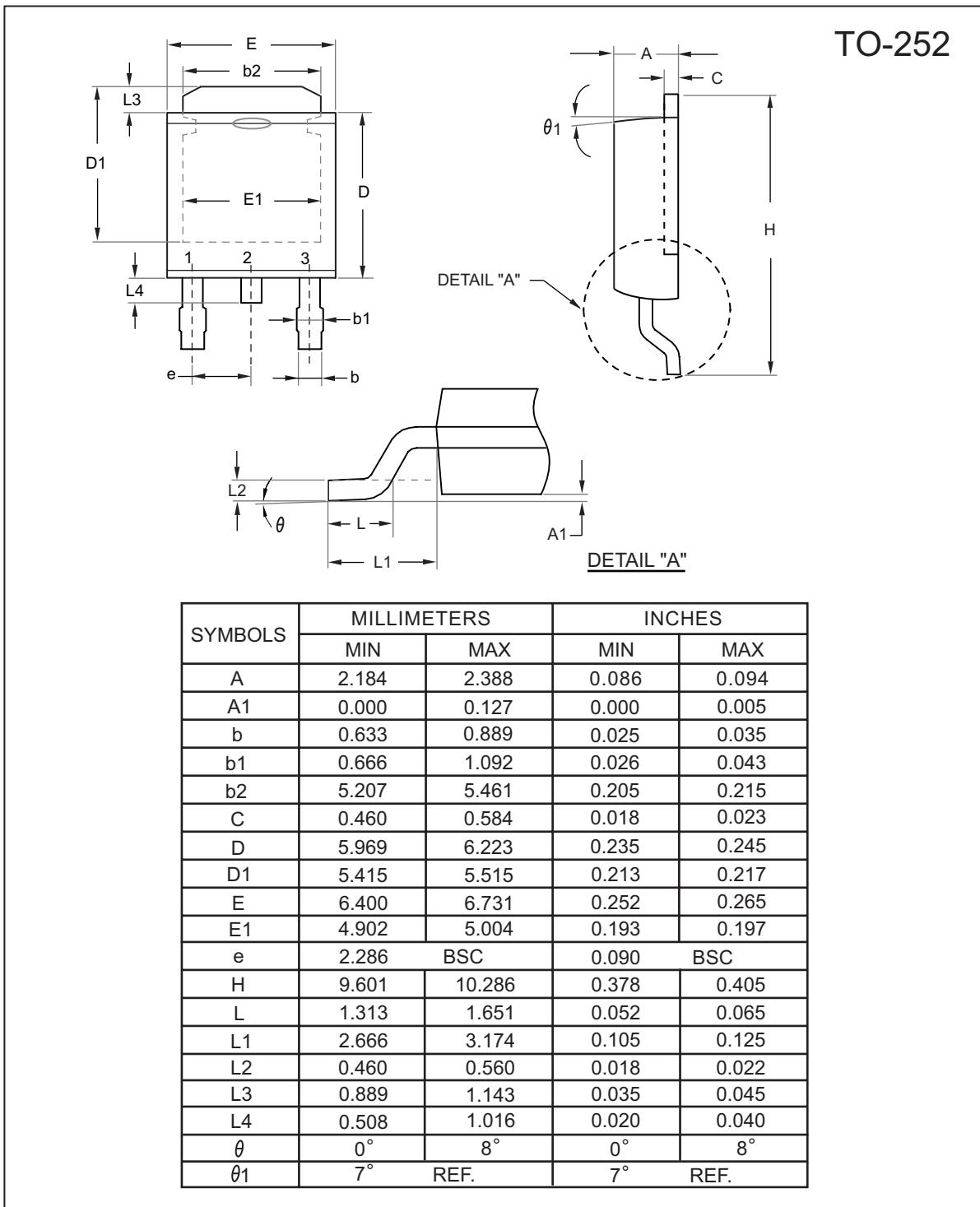
TO-251



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0.032
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

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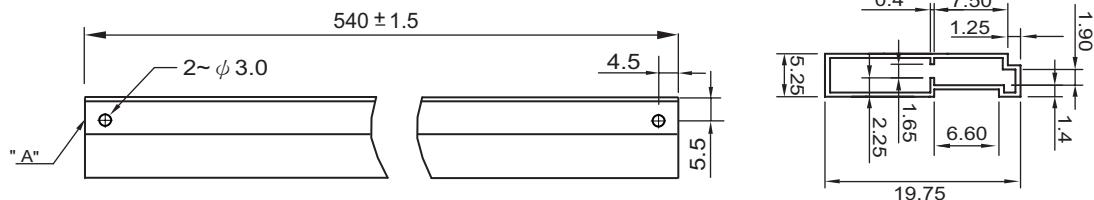


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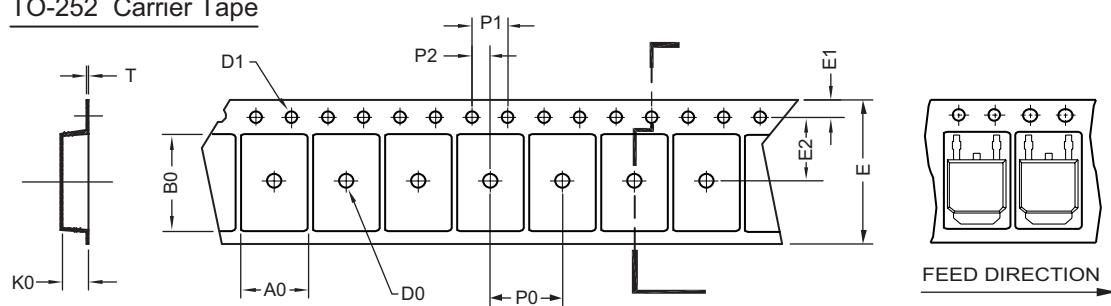
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## TO-251 Tube/TO-252 Tape and Reel Data

### TO-251 Tube



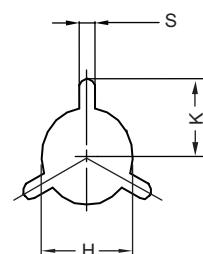
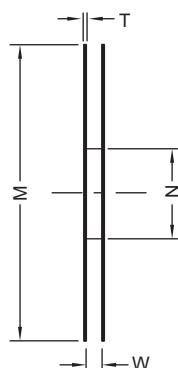
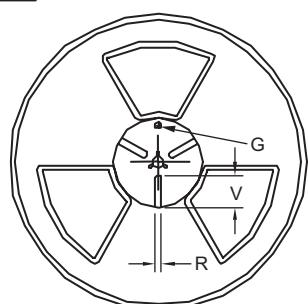
### TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	ψ 2	ψ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

### TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	ψ 330	ψ 330 ± 0.5	ψ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ψ 13.0 + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---

Aug,17,2012